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A2  
09/615,474, filed on July 13, 2000; which is a continuation application of U.S. Patent Application Serial No. 09/324,299, filed on June 2, 1999, and now U.S. Patent 6,113,761.

Please replace the paragraph beginning at line 32 of page 4 with the following clean replacement paragraphs in accordance with 37 C.F.R. § 1.121(b)(1)(ii):

FIG. 10 is a photomicrograph of a Cu target, CuCr intermediate layer and an Al backing plate;

A3  
FIG. 11 is a photomicrograph of a Cu target, CuCr intermediate layer and an Al backing plate; and

Please replace the paragraph starting at line 6 on page 19 with the following clean replacement paragraph:

A4  
The invention includes a method of forming a sputtering target containing copper of a purity of at least about 99.999 wt.%, and at least one component selected from the group consisting of Ag, Sn, Te, In, B, Bi, Sb, and P dispersed within the copper. The total of Ag, Sn, Te, In, B, Bi, Sb, and P within the copper is from at least 0.3 ppm to about 10 ppm. The sputtering target has a substantially uniform grain size of less than or equal to about 50 micrometers throughout the copper and the at least one component.

### In The Claims

Please cancel claims 1-9 and 14-17. Please add new claims 18-22.

A marked up version showing amendments to any claims being changed is provided in one or more accompanying pages separate from this amendment in accordance with 37 C.F.R. § 1.121(c)(1)(ii). Any claim not accompanied by a marked up version has not been